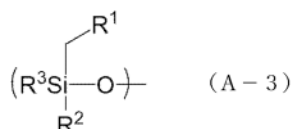
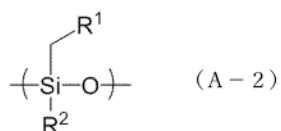
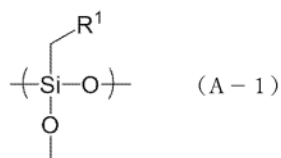


Title of Invention - COMPOSITION FOR FORMING SILICON-
CONTAINING RESIST FILM AND PATTERNING PROCESS

ABSTRACT

The present invention is a composition for forming a silicon-containing resist film contains a polysiloxane containing at least one of any of a repeating unit represented by formula (A-1), a repeating unit represented by formula (A-2), or a substructure represented by formula (A-3):



wherein R¹ is a monovalent organic group, a halogen atom, a hydroxy group, a sulfo group, a nitro group, or a carboxyl group, functioning as a group eliminated by heat, acid, or base, and R² and R³ represent a monovalent organic group. The present invention can provide a composition for forming a silicon-containing resist film such that an ultra-fine resist pattern with excellent LWR (line width roughness) and CDU (critical dimension uniformity) can be formed.

[FIGURE: NONE]